



# PSMNR90-30BL

N-channel 30 V 1.1 m $\Omega$  logic level MOSFET in D2PAK

Rev. 1 — 27 September 2011

Objective data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	<a href="#">11</a>	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	306	W
$T_j$	junction temperature		-55	-	175	°C

#### Static characteristics

$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 12</a>	-	0.92	1.1	m $\Omega$
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 100\text{ °C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>	-	1.19	1.5	m $\Omega$



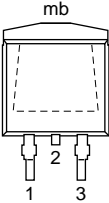
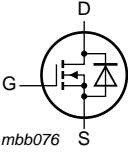
**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 75\text{ A};$	-	37	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{DS} = 15\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	118	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(\text{AL})S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C};$ $I_D = 120\text{ A}; V_{\text{sup}} \leq 30\text{ V};$ $R_{GS} = 50\text{ }\Omega;$ unclamped	-	-	1.9	J

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;"><b>SOT404 (D2PAK)</b></p>	 <p style="text-align: center;"><i>mbb076</i></p>
2	D	drain <sup>[1]</sup>		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
PSMNR90-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

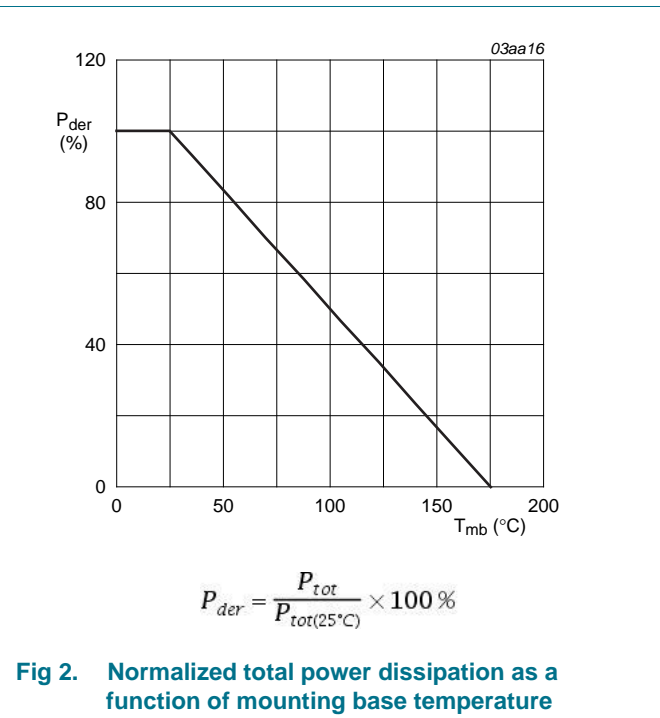
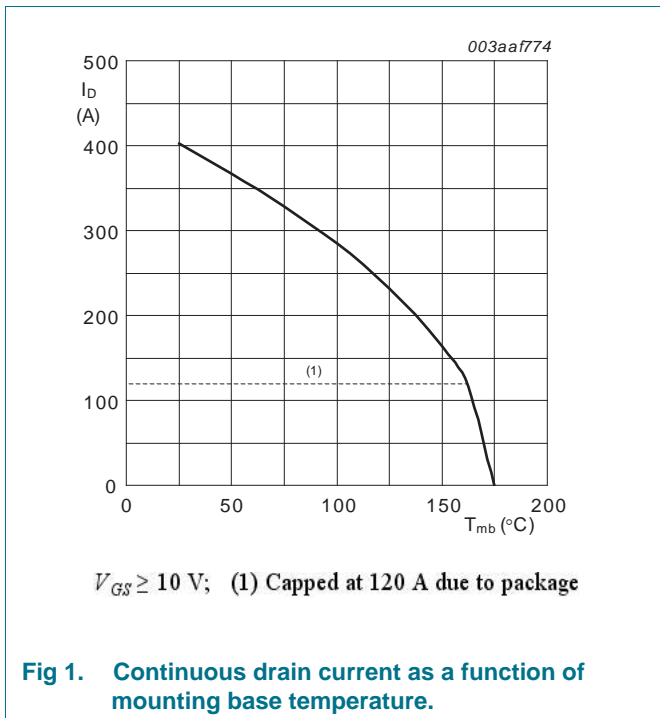
### 4. Limiting values

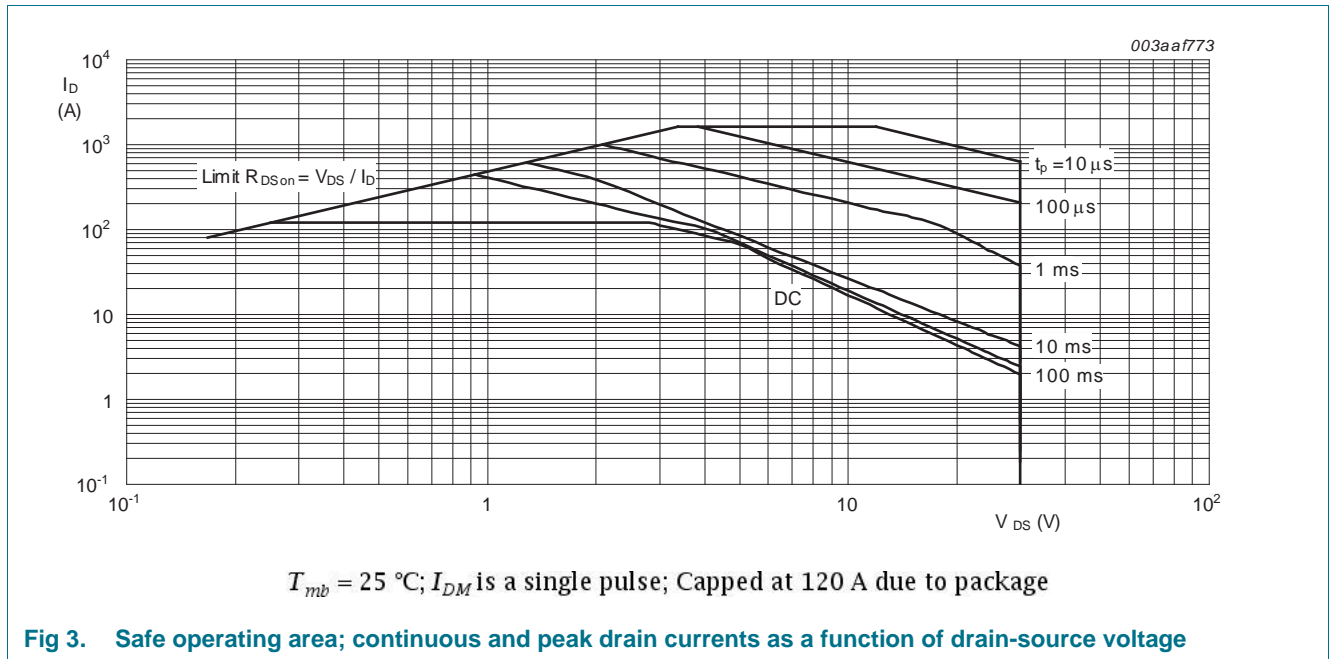
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>	[1]	120	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a>	[1]	120	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 3</a>	-	1573	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	306	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>slid(M)</sub>	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	1573	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; unclamped	-	1.9	J

[1] Continuous current is limited by package.

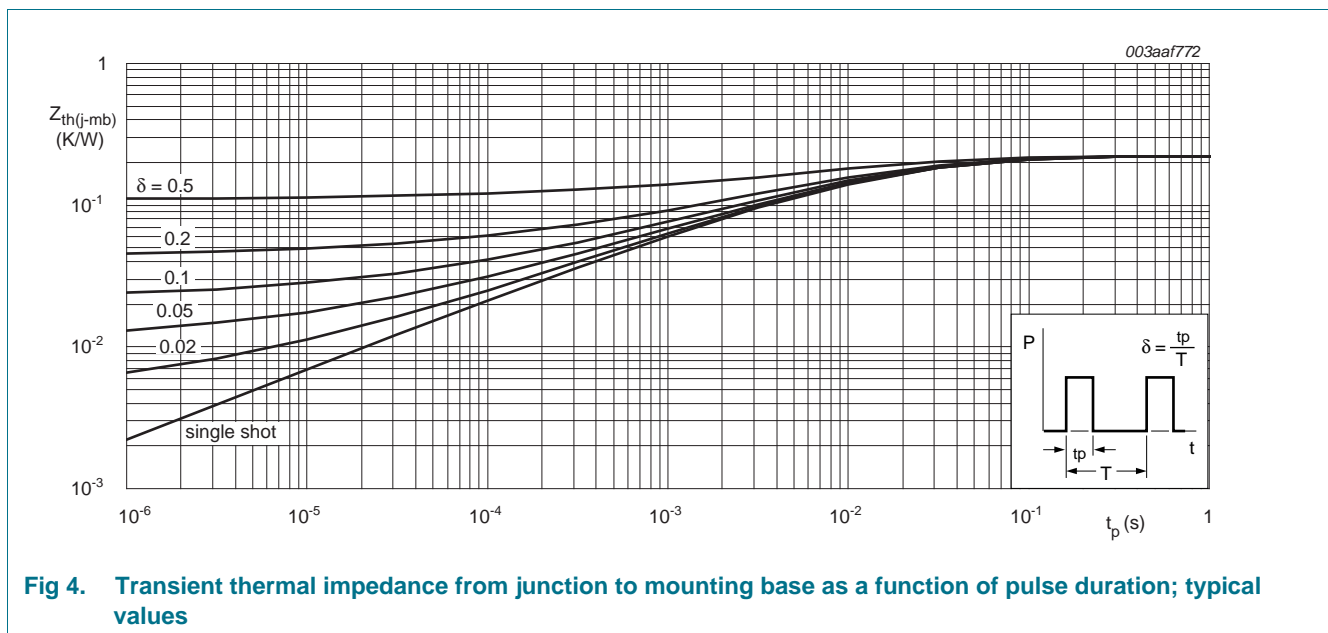




### 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.22	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values**

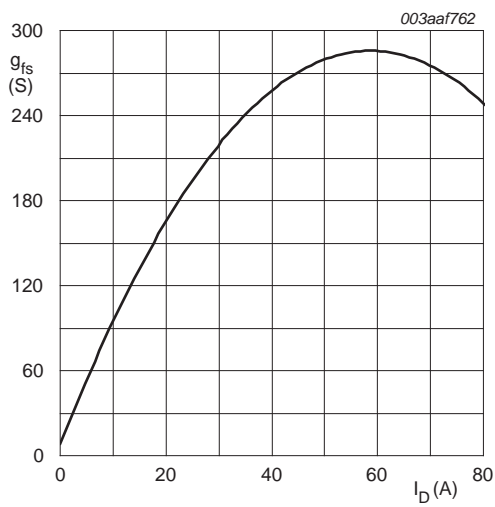
## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	1.3	1.7	2.2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	-	-	2.5	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	10	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{Dson}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	0.92	1.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	1.1	1.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>	-	1.65	2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>	-	1.19	1.5	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	1.1	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	243	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	222	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	118	-	nC
$Q_{GS}$	gate-source charge		-	39	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	22	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	17	-	nC
$Q_{GD}$	gate-drain charge		-	37	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 75 \text{ A}; V_{DS} = 15 \text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	2.8	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	14850	-	pF
$C_{oss}$	output capacitance		-	2799	-	pF
$C_{riss}$	reverse transfer capacitance		-	1215	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.2 \text{ }^\circ\Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \text{ }^\circ\Omega; I_D = 75 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	95	-	ns
$t_r$	rise time	$V_{DS} = 15 \text{ V}; R_L = 0.2 \text{ }^\circ\Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}; I_D = 75 \text{ A}$	-	213	-	ns

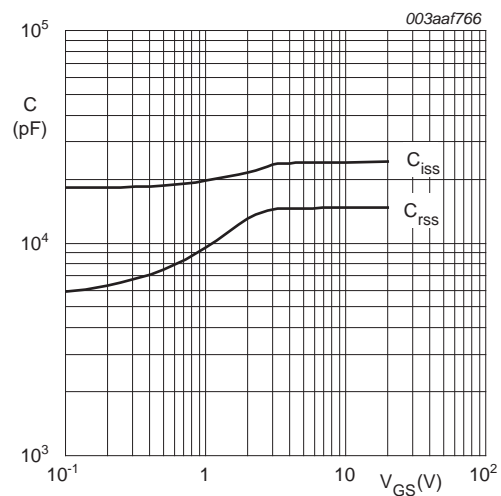
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(off)}$	turn-off delay time	$V_{DS} = 15\text{ V}; R_L = 0.2\ \Omega; V_{GS} = 5\text{ V};$	-	199	-	ns
$t_f$	fall time	$R_{G(ext)} = 5\ \Omega; I_D = 75\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	115	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 17</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s};$	-	67	-	ns
$Q_r$	recovered charge	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}$	-	123	-	nC



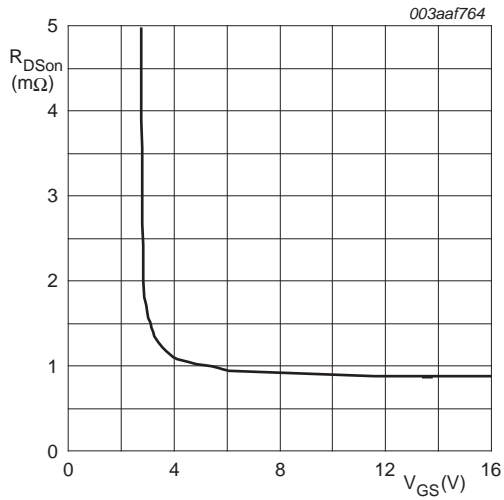
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 15\text{ V}$

Fig 5. Forward transconductance as a function of drain current; typical values



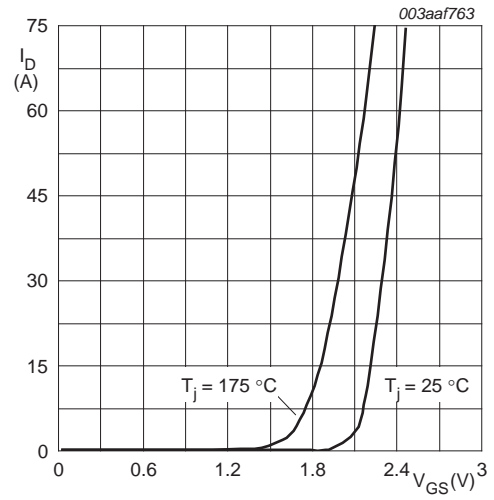
$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



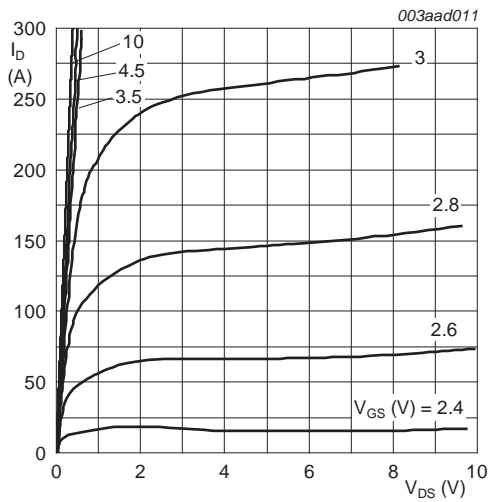
$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



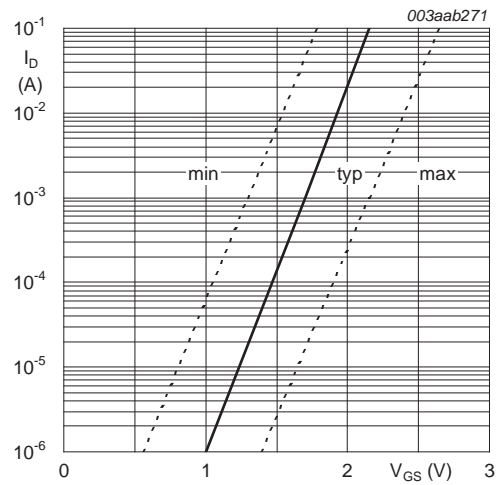
$V_{DS} > I_D \times R_{DS(on)}$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25^\circ\text{C}$

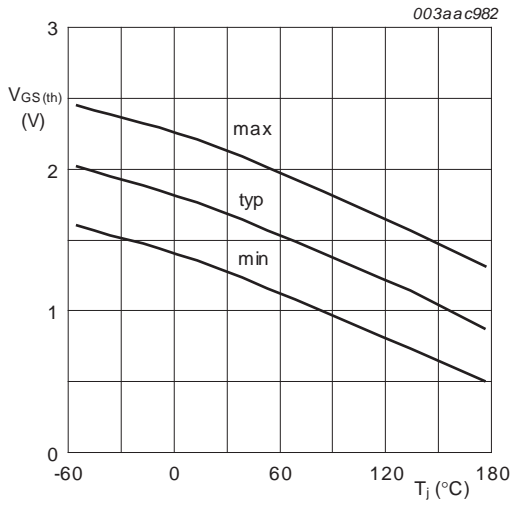
Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



$T_j = 25^\circ\text{C}; V_{DS} = 5\text{ V}$

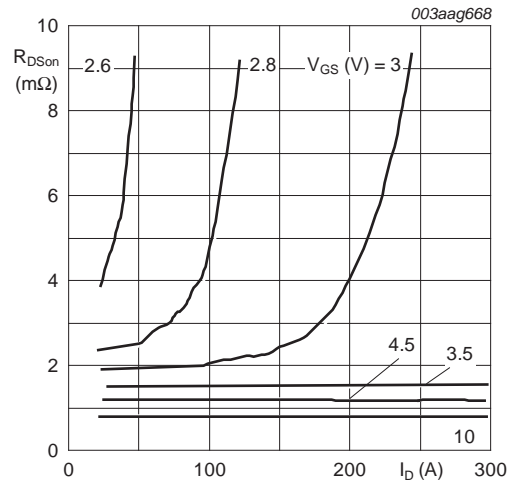
Fig 10. Sub-threshold drain current as a function of gate-source voltage





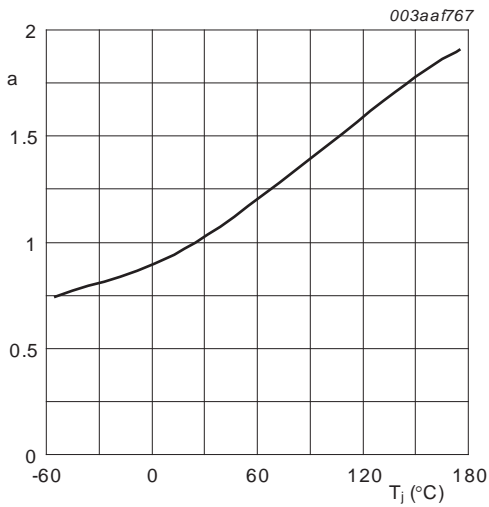
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

Fig 11. Gate-source threshold voltage as a function of junction temperature



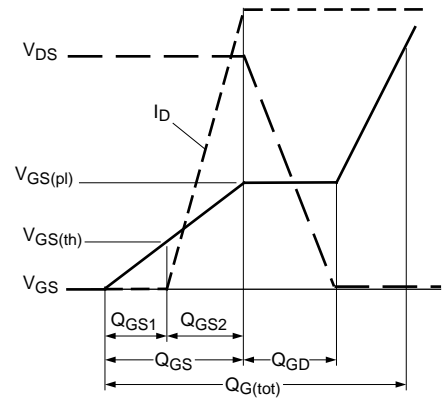
$$T_j = 25^\circ\text{C}$$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



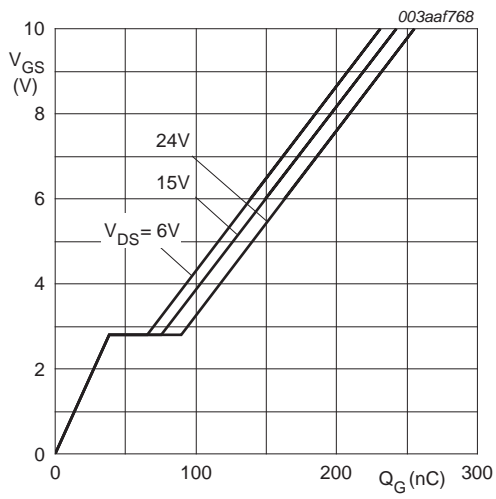
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



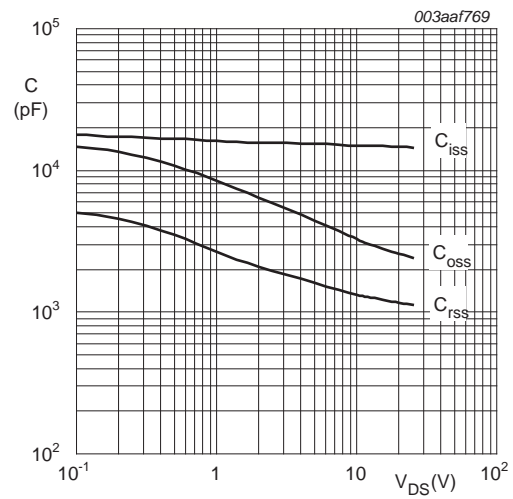
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Fig 14. Gate charge waveform definitions



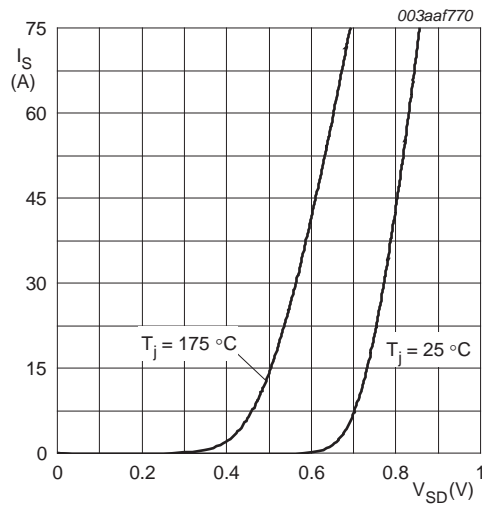
$T_j = 25\text{ °C}; I_D = 75\text{ A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

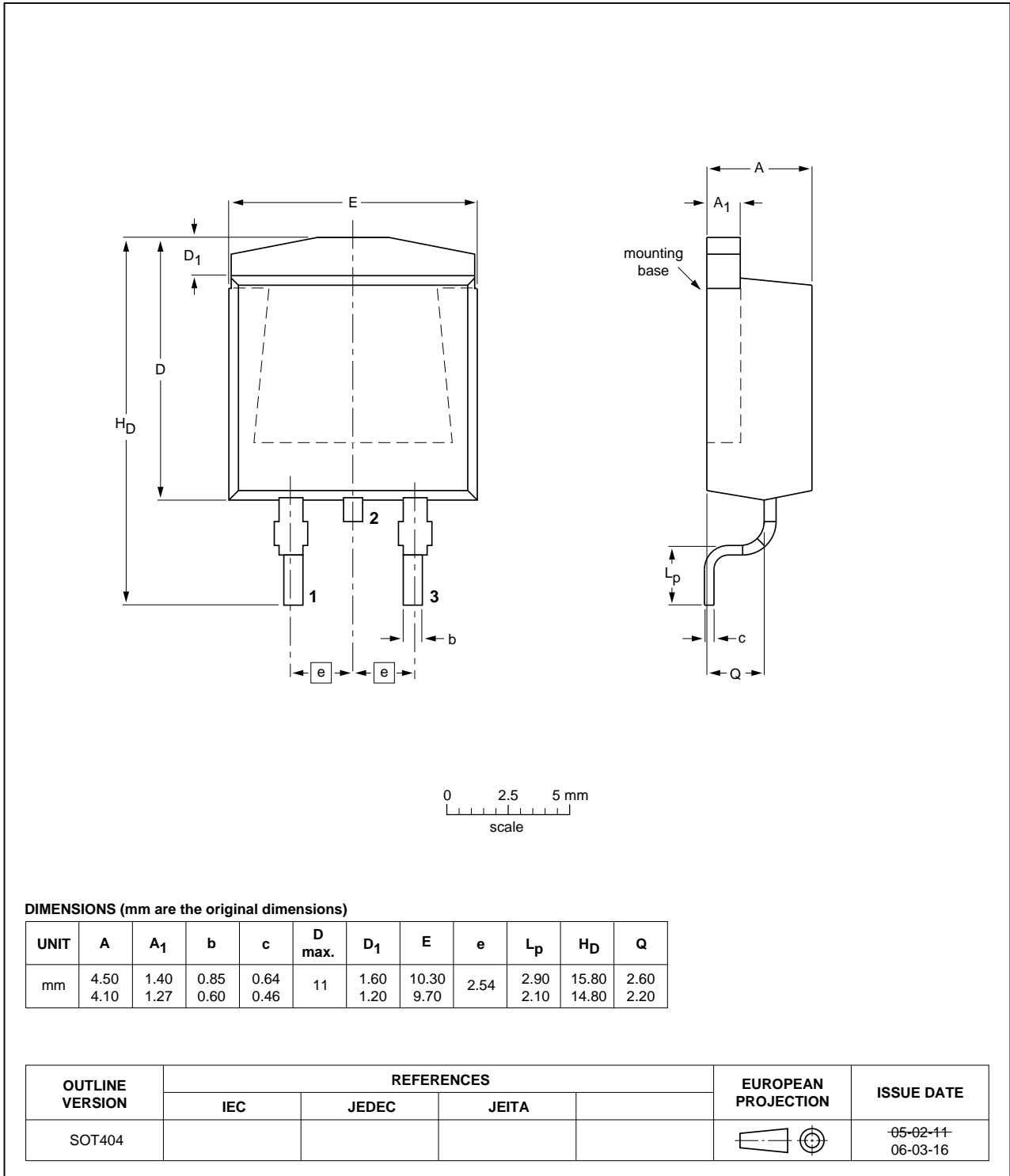


Fig 18. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMNR90-30BL v.1	20110927	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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